

MOS FIELD EFFECT TRANSISTORS
2SK2369/2SK2370

SWITCHING
 N-CHANNEL POWER MOS FET
 INDUSTRIAL USE

DESCRIPTION

The 2SK2369/2SK2370 is N-Channel MOS Field Effect Transistor designed for high voltage switching applications.

FEATURES

- Low On-Resistance
 2SK2369: $R_{DS(on)} = 0.35 \Omega$ ($V_{GS} = 10 V, I_D = 10 A$)
 2SK2370: $R_{DS(on)} = 0.4 \Omega$ ($V_{GS} = 10 V, I_D = 10 A$)
- Low C_{iss} $C_{iss} = 2400 pF$ TYP.
- High Avalanche Capability Ratings

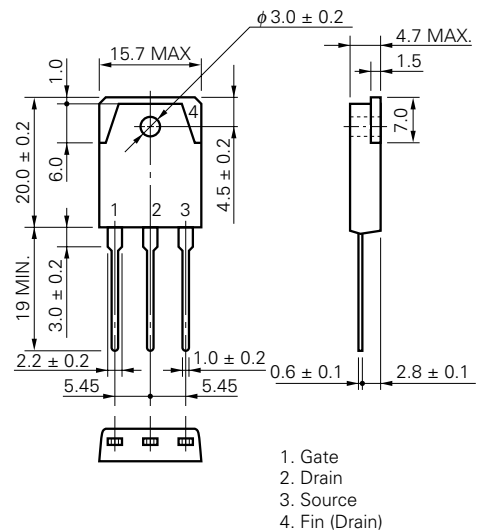
ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$)

Drain to Source Voltage(2SAK2369/2370)	V_{BSS}	450/500	V
Gate to Source Voltage	V_{GSS}	± 30	V
Drain Current (DC)	$I_D(DC)$	± 20	A
Drain Current (pulse)*	$I_D(pulse)$	± 80	A
Total Power Dissipation ($T_c = 25^\circ C$)	P_{T1}	140	W
Total Power Dissipation ($T_A = 25^\circ C$)	P_{T2}	3.0	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$
Single Avalanche Current**	I_{AS}	20	A
Single Avalanche Energy**	E_{AS}	285	mJ

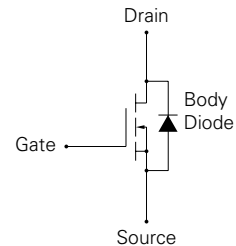
* $PW \leq 10 \mu s$, Duty Cycle $\leq 1\%$

** Starting $T_{ch} = 25^\circ C$, $R_G = 25 \Omega$, $V_{GS} = 20 V \rightarrow 0$

PACKAGE DIMENSIONS
 (in millimeters)



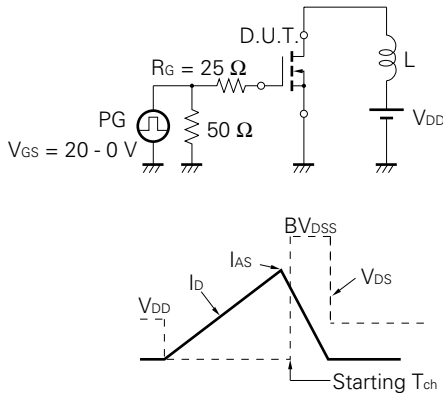
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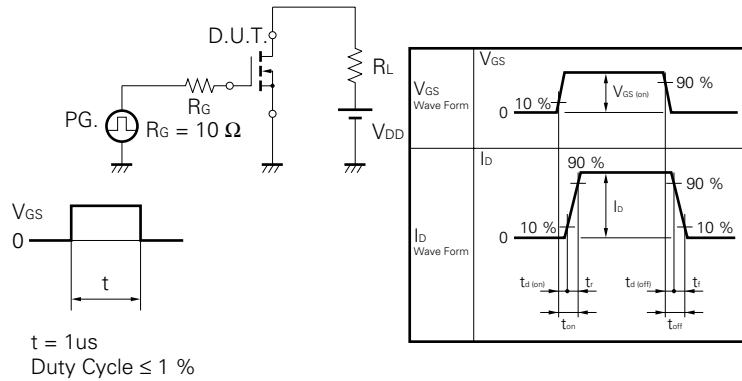
ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain to Source On-State Resistance	R _{DS(on)}		0.30	0.35	Ω	V _{GS} = 10 V
			0.32	0.40		I _D = 10 V
Gate to Source Cutoff Voltage	V _{GS(off)}	2.5		3.5	V	V _{DS} = 10 V, I _D = 1 mA
Forward Transfer Admittance	y _{fs}	7.5			S	V _{DS} = 10 V, I _D = 10 A
Drain Leakage Current	I _{DSS}			100	μA	V _{DS} = V _{DSS} , V _{GS} = 0
Gate to Source Leakage Current	I _{GSS}			±100	nA	V _{GS} = ±30 V, V _{DS} = 0
Input Capacitance	C _{iss}		2400		pF	V _{DS} = 10 V
Output Capacitance	C _{oss}		500		pF	V _{GS} = 0
Reverse Transfer Capacitance	C _{rss}		45		pF	f = 1 MHz
Turn-On Delay Time	t _{d(on)}		35		ns	I _D = 10 A
Rise Time	t _r		60		ns	V _{GS} = 10 V
Turn-Off Delay Time	t _{d(off)}		105		ns	V _{DD} = 150 V
Fall Time	t _f		65		ns	R _G = 10 Ω R _L = 15 Ω
Total Gate Charge	Q _G		65		nC	I _D = 20 A
Gate to Source Charge	Q _{GS}		15		nC	V _{DD} = 400 V
Gate to Drain Charge	Q _{GD}		30		nC	V _{GS} = 10 V
Body Diode Forward Voltage	V _{F(S-D)}		1.0		V	I _F = 20 A, V _{GS} = 0
Reverse Recovery Time	t _{rr}		500		ns	I _F = 20 A, V _{GS} = 0
Reverse Recovery Charge	Q _{rr}		3.5		μC	di/dt = 50 A/μs

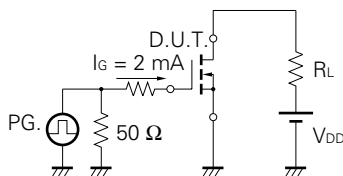
Test Circuit 1 Avalanche Capability



Test Circuit 2 Switching Time

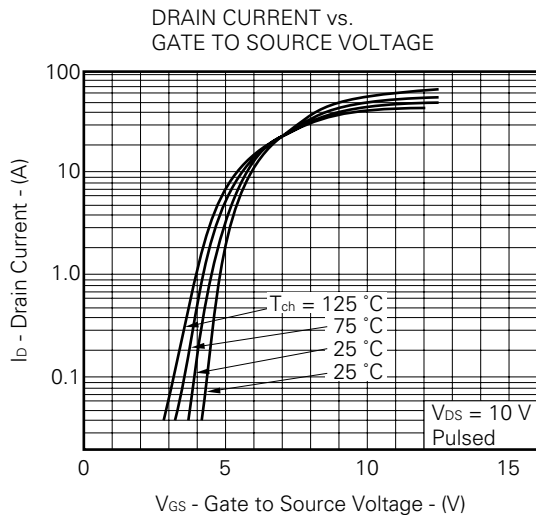
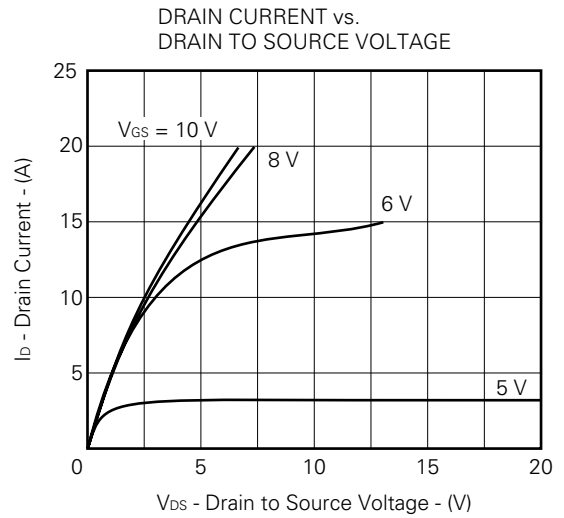
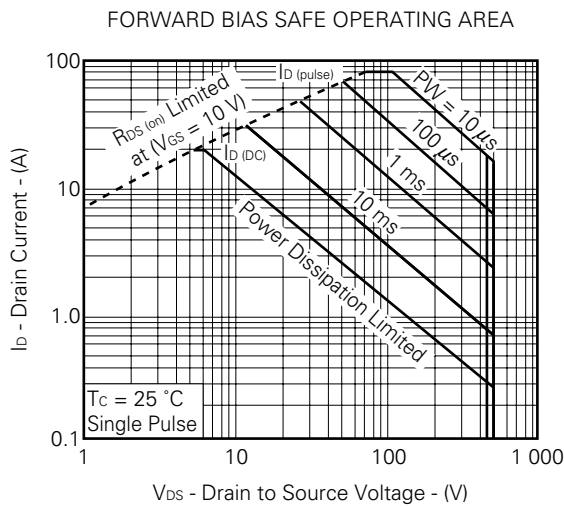
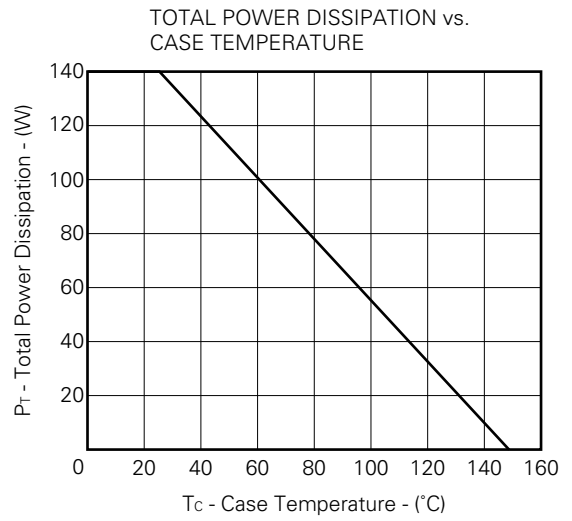
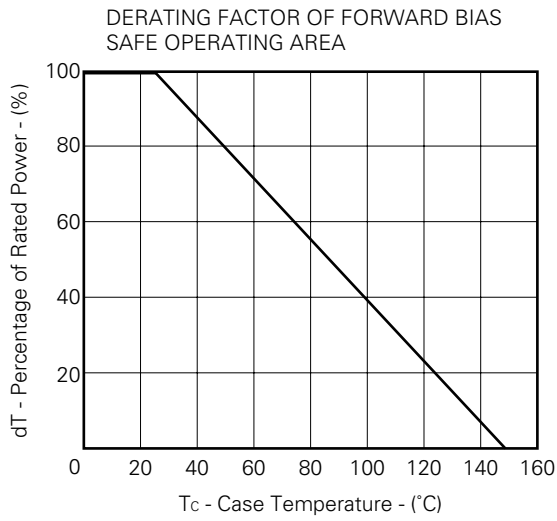


Test Circuit 3 Gate Charge

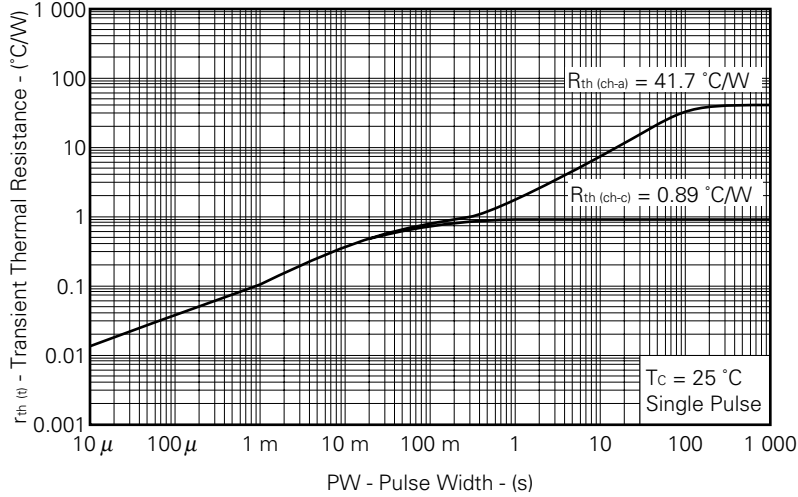


The application circuits and their parameters are for references only and are not intended for use in actual design-in's.

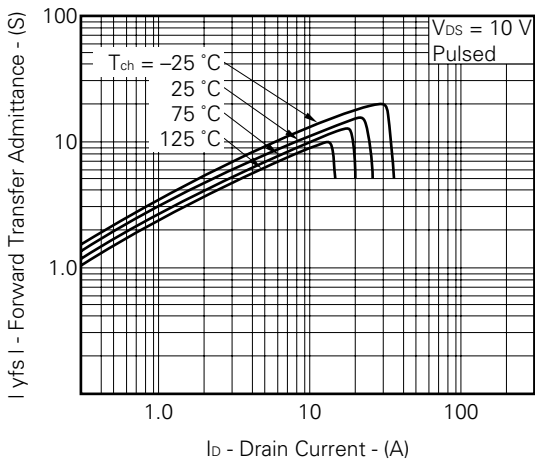
TYPICAL CHARACTERISTICS (T_A = 25 °C)



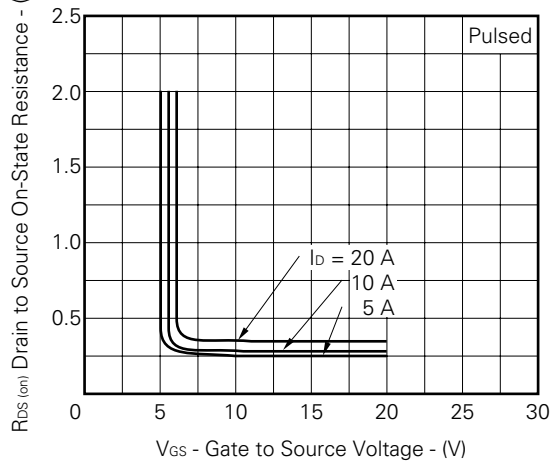
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



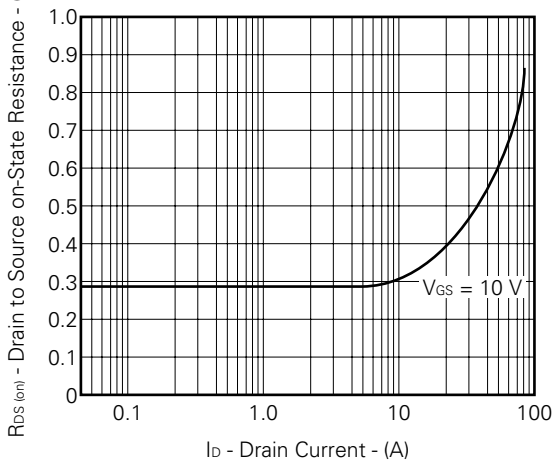
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



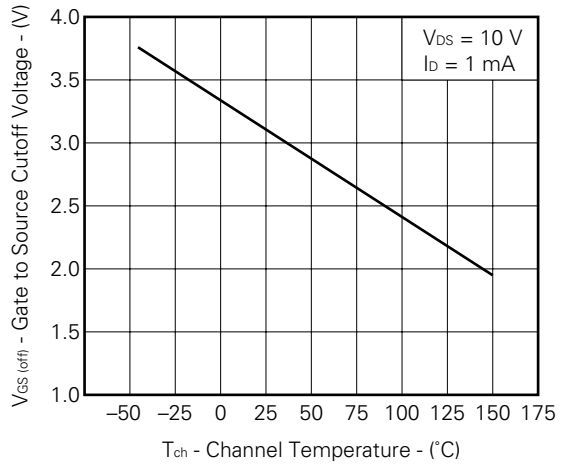
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

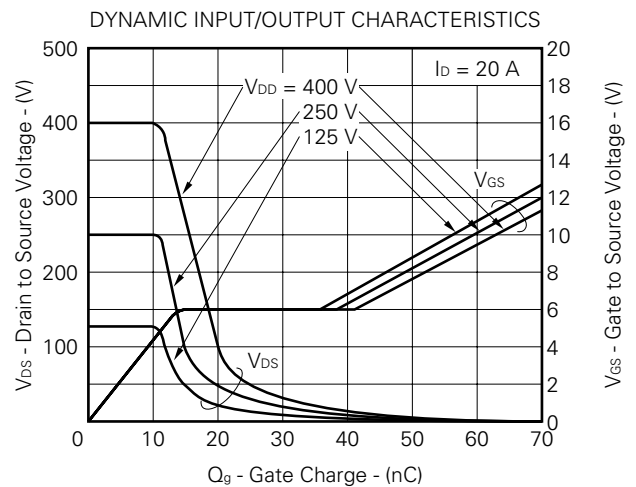
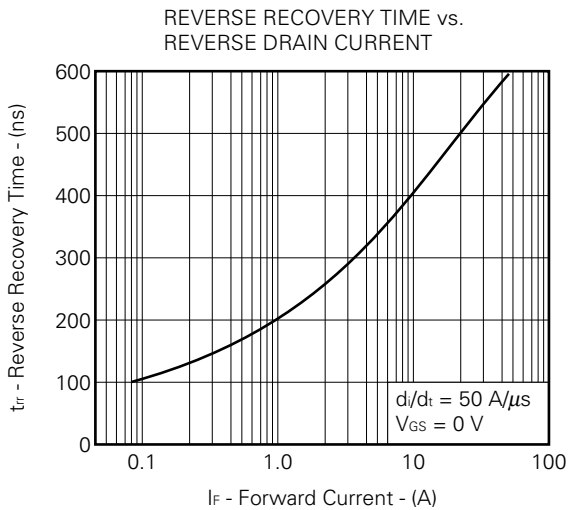
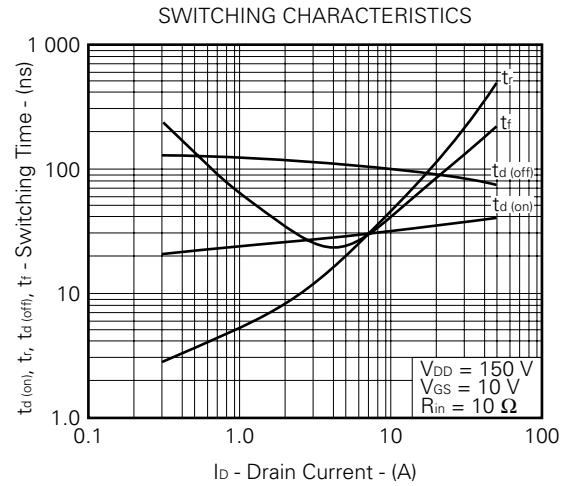
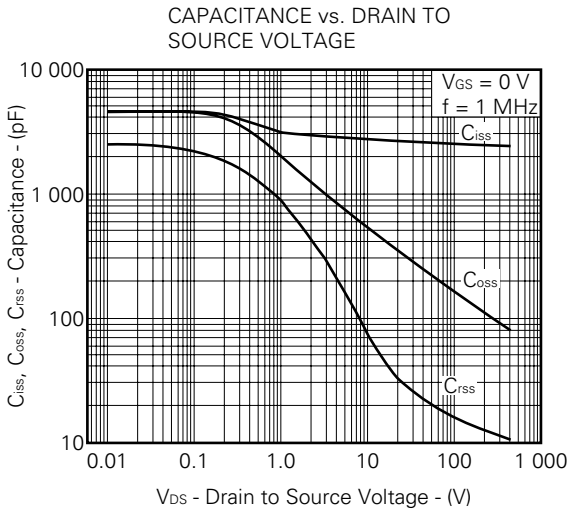
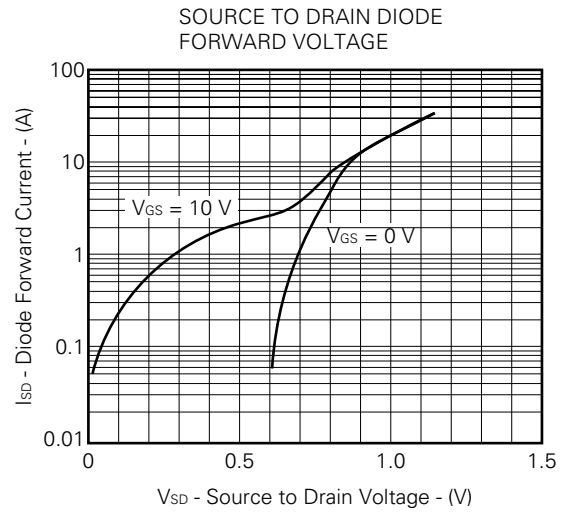
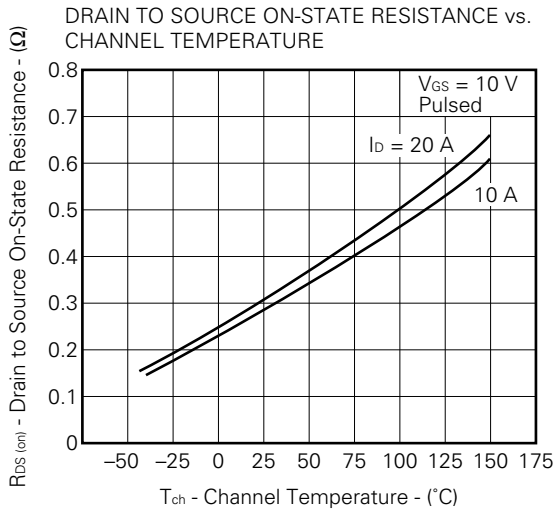


DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

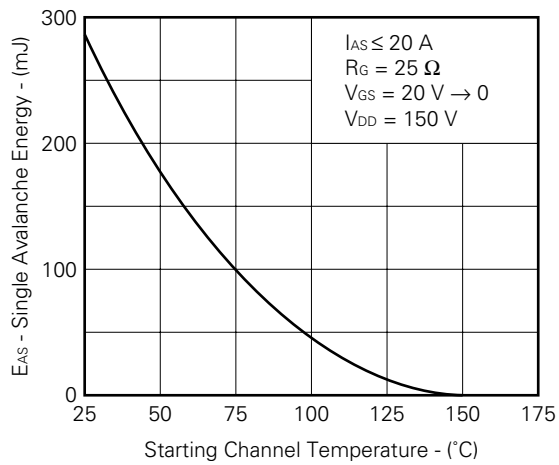


GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE





SINGLE AVALANCHE ENERGY vs. STARTING CHANNEL TEMPERATURE



SINGLE AVALANCHE ENERGY vs. INDUCTIVE LOAD

